

TECHNICAL DATA DATA SHEET 4648, REV. -

HERMETIC SCHOTTKY RECTIFIER Low Forward Voltage Drop

Features:

- Soft Reverse Recovery at Low and High Temperature
- Low Forward Voltage Drop
- Low Power Loss, High Efficiency
- High Surge Capacity
- Guard Ring for Enhanced Durability and Long Term Reliability
- Guaranteed Reverse Avalanche Characteristics

Maximum Ratings

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	200	V
Max. Average Forward Current	I _{F(AV)}	50% duty cycle, rectangular wave form (Single)	3.0	А
Max. Average Forward Current	I _{F(AV)}	50% duty cycle, rectangular wave form (Common Cathode)	6	А
Max. Peak One Cycle Non- Repetitive Surge Current	I _{FSM}	8.3 ms, half Sine wave (per leg)	55	А
Non-Repetitive Avalanche Energy	E _{AS}	$T_J = 25 ^{\circ}\text{C}, I_{AS} = 3.0 \text{A},$ L = 4.4 mH (per leg)	20	mJ
Repetitive Avalanche Current	I _{AR}	I _{AS} decay linearly to 0 in 1 μs f limited by T _J max V _A =1.5V _R	3.0	Α
Maximum Thermal Resistance	$R_{ ext{ hetaJC}}$	(Single) (Common Cathode)	2.97 5.95	°C/W
Max. Junction Temperature	TJ	-	-65 to +200	°C
Max. Storage Temperature	T _{stg}	-	-65 to +200	°C

Electrical Characteristics

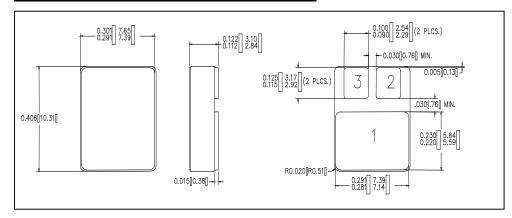
Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	V_{F1}	@ 3.0A, Pulse, T _J = 25 °C	0.97	V
(per leg)	V_{F2}	@ 3.0A, Pulse, T _J = 125 °C	0.81	V
Max. Reverse Current	I _{R1}	@V _R = 200V, Pulse,	0.07	mA
		$T_J = 25 ^{\circ}C$		
(per leg)	I_{R2}	@V _R = 200V, Pulse,	1.6	mA
		T _J = 125 °C		
Max. Junction Capacitance	C _T	$@V_R = 5V, T_C = 25 ^{\circ}C$	60	pF
(per leg)		$f_{SIG} = 1MHz,$		
		$V_{SIG} = 50 \text{mV (p-p)}$		

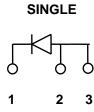


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Mechanical Dimensions: in Inches / mm

LCC-5





PINOUT TABLE

0.0

0.2

0.4

0.6

Forward Voltage Drop - V_F (V)

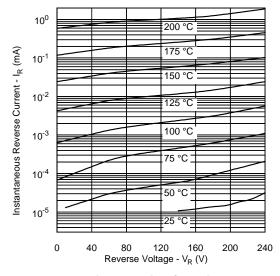
DEVICE TYPE	PIN 1	PIN 2	PIN 3
SINGLE RECTIFIER	CATHODE	ANODE	ANODE

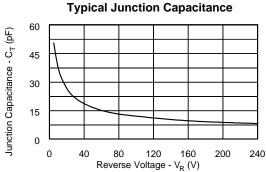
Note: The V_f curves shown are for the SD60SC200 unpackaged die only.

Typical Forward Characteristics

10° 200° C 175° C 125° C 125° C 10°3

Typical Reverse Characteristics





1.0



TECHNICAL DATA

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